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PMR400UN

N-channel TrenchMOS ultra low level FET

Rev. 2 — 2 February 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in ultra small Surface-Mounted Device (SMD) plastic package using TrenchMOS technology.

1.2 Features and benefits

- Low threshold voltage
- Surface mounted package
- Low on-state resistance
- Footprint 63% smaller than SOT23

1.3 Applications

Driver circuits

Switching in portable appliances

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	30	V
I _D	drain current	$T_{sp} = 25 ^{\circ}C; V_{GS} = 4.5 V$	-	-	8.0	Α
V_{GS}	gate-source voltage		-8	-	8	V
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 25 \text{ °C}$	-	400	480	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	П.	D
2	S	source		
3	D	drain	1	G S 017aaa253



N-channel TrenchMOS ultra low level FET

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMR400UN	SC-75	plastic surface-mounted package; 3 leads	SOT416

4. Marking

Table 4. Marking codes

Type number	Marking code
PMR400UN	R7

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	30	V
drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
gate-source voltage		-8	8	V
drain current	$T_{sp} = 25 ^{\circ}\text{C}; V_{GS} = 4.5 \text{V}$	-	0.8	Α
	$T_{sp} = 100 ^{\circ}\text{C}; V_{GS} = 4.5 \text{V}$	-	0.51	Α
peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$	-	1.61	Α
total power dissipation	T _{sp} = 25 °C	-	0.53	W
storage temperature		-55	150	°C
junction temperature		-55	150	°C
n diode				
source current	T _{sp} = 25 °C	-	0.44	Α
peak source current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$	-	0.88	Α
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature n diode source current	$\begin{array}{ll} \text{drain-source voltage} & T_j \geq 25 \text{ °C}; \ T_j \leq 150 \text{ °C} \\ \text{drain-gate voltage} & T_j \geq 25 \text{ °C}; \ T_j \leq 150 \text{ °C}; \ R_{GS} = 20 \text{ k}\Omega \\ \text{gate-source voltage} \\ \text{drain current} & T_{sp} = 25 \text{ °C}; \ V_{GS} = 4.5 \text{ V} \\ \hline T_{sp} = 100 \text{ °C}; \ V_{GS} = 4.5 \text{ V} \\ \text{peak drain current} & T_{sp} = 25 \text{ °C}; \ \text{pulsed}; \ t_p \leq 10 \mu\text{s} \\ \text{total power dissipation} & T_{sp} = 25 \text{ °C} \\ \text{storage temperature} \\ \text{junction temperature} \\ \hline \textbf{n diode} \\ \text{source current} & T_{sp} = 25 \text{ °C} \\ \end{array}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

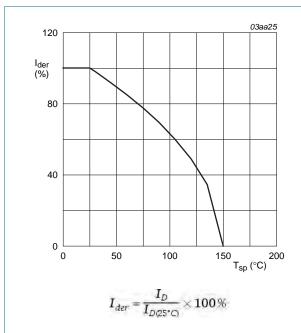


Fig 1. Normalized continuous drain current as a function of solder point temperature

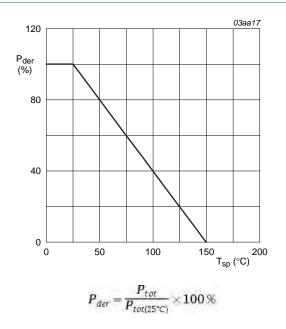


Fig 2. Normalized total power dissipation as a function of solder point temperature

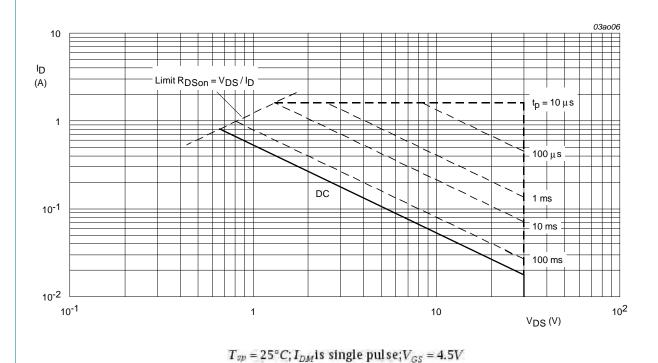


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

N-channel TrenchMOS ultra low level FET

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Mi	in	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-		-	235	K/W

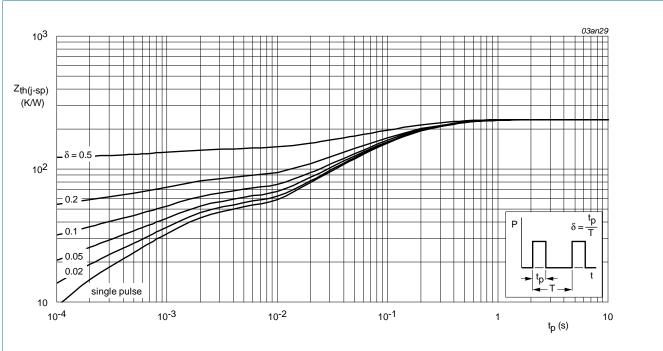


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

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7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 1 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 1 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold	$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	1	V
	voltage	$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.25	-	-	V
		$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	1.2	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R_{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 25 \text{ °C}$	-	400	480	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 150 \text{ °C}$	-	660	816	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	480	580	mΩ
		$V_{GS} = 1.8 \text{ V}; I_D = 0.075 \text{ A}; T_j = 25 \text{ °C}$	-	580	830	mΩ
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 1 A; V_{DS} = 15 V; V_{GS} = 4.5 V;$	-	0.89	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	43	-	pF
Coss	output capacitance	T _j = 25 °C	-	7.7	-	pF
C _{rss}	reverse transfer capacitance		-	4.8	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 15 Ω ; V_{GS} = 4.5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7.5	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	4.5	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 0.3 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-	0.76	1.2	V

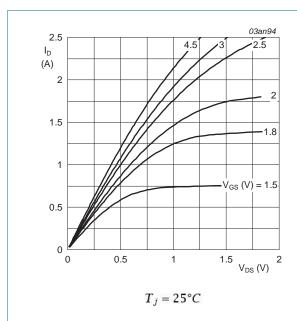


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

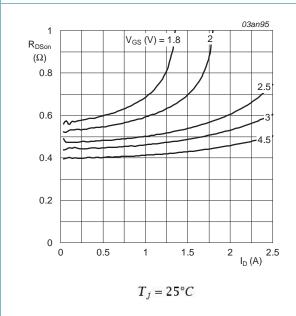
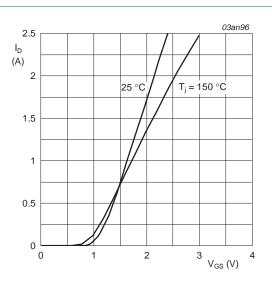


Fig 7. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25$ °C and 150°C; $V_{DS} > I_D \times R_{DSON}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

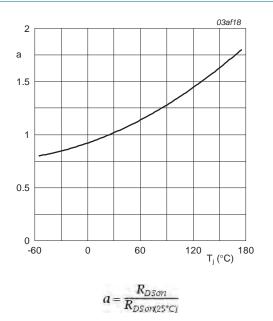


Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature

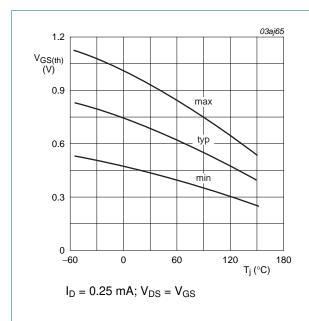


Fig 9. Gate-source threshold voltage as a function of junction temperature

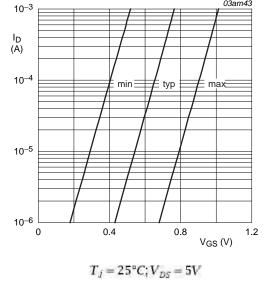


Fig 10. Sub-threshold drain current as a function of gate-source voltage

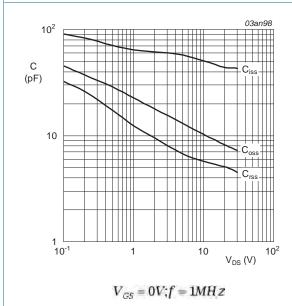
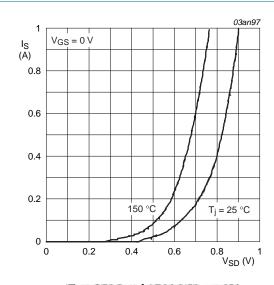


Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C \text{ and } 150^{\circ}C; V_{GS} = 0V$

Fig 12. Source current as a function of source-drain voltage; typical values

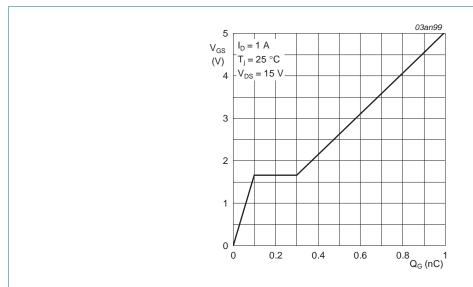
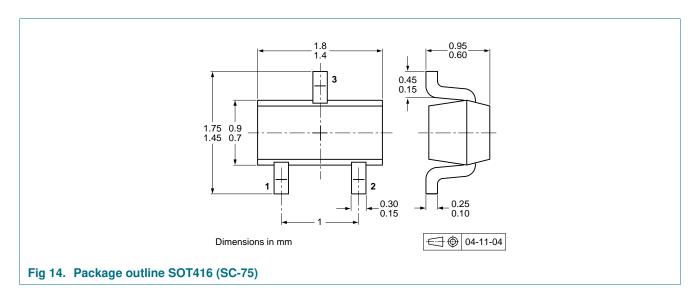


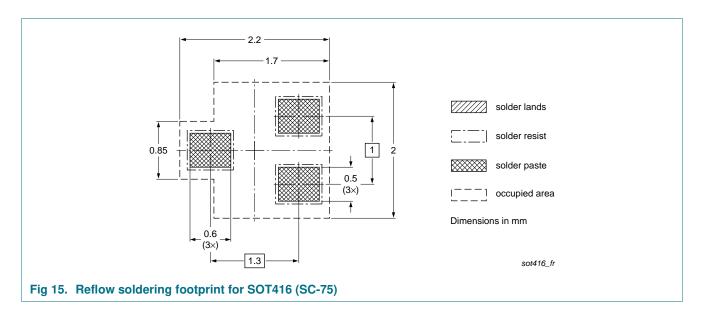
Fig 13. Gate-source voltage as a function of gate charge; typical values

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8. Package outline



9. Soldering



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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PMR400UN v.2	20120202	Product data sheet	-	PMR400UN v.1	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines NXP Semiconductors. 				
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.	
PMR400UN v.1	20040303	Product data sheet	-	-	

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11.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel TrenchMOS ultra low level FET

13. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information1
3	Ordering information2
4	Marking2
5	Limiting values2
6	Thermal characteristics4
7	Characteristics5
8	Package outline9
9	Soldering9
10	Revision history10
11	Legal information11
11.1	Data sheet status
11.2	Definitions11
11.3	Disclaimers
11.4	Trademarks12
12	Contact information12

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